

PATENT ABSTRACTS OF JAPAN

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(54) FORMATION OF RESIST PATTERN

(57)Abstract:

PURPOSE: To make it possible to the stop, be gentle which is generated by a stepped approximation, of a resist pattern without increasing a data processing time and the time of exposure and to approximate the resist pattern to a targeted pattern to hardly effect to the characteristics of the resist pattern.

CONSTITUTION: The reference focal point of radioactive rays, which is decided by an exposure device, is shifted by a prescribed amount from design data 1 on the basis of exposure data 2, which is approximated stepwise from the data 1 by the exposure device, to perform an exposure on a resist and thereafter, the resist is subjected to developing treatment to form a resist pattern 3.

